

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously presented) A polycrystalline silicon substrate for use in a photoelectric conversion element, comprising a region which contains concentrations of impurities that satisfy the following relations:

$[O_i] \geq 2E17$ [atoms/cm³] (Condition 1a) and

$[C] \leq E17$ [atoms/cm³] (Condition 2)

where $[O_i]$ is an interstitial oxygen concentration determined by Fourier transform infrared spectroscopy and $[C]$ is a total carbon concentration determined by secondary ion mass spectrometry;

wherein the polycrystalline silicon substrate is doped with boron.

2. (Original) A polycrystalline silicon substrate according to claim 1, wherein the substrate is sliced out from an ingot.

3. (Original) A polycrystalline silicon substrate according to claim 2, wherein the substrate satisfies the Condition 1a and the Condition 2 at all regions excluding a 1 cm wide peripheral edge portion.

4. (Previously presented) A polycrystalline silicon substrate for use in a photoelectric conversion element, comprising a region which contains concentrations of impurities that satisfy the following relations:

$[O_i] + 30 \times [N] \geq 2E17$ [atoms/cm³] (Condition 1b) and

$[C] \leq 1E17$ [atoms/cm³] (Condition 2)

wherein $[O_i]$ is an interstitial oxygen concentration determined by Fourier transform infrared spectroscopy, $[N]$ is a total nitrogen concentration determined by

second ion mass spectrometry, and [C] is a total carbon concentration determined by secondary ion mass spectrometry;

wherein the polycrystalline silicon substrate is doped with boron.

5. (Original) A polycrystalline silicon substrate according to claim 4, wherein the substrate is sliced out from an ingot.

6. (Original) A polycrystalline silicon substrate according to claim 5, wherein the substrate satisfies the Condition 1b and the Condition 2 at all regions excluding a 1 cm wide peripheral edge portion.

7. (Previously presented) A polycrystalline silicon ingot for use in a photoelectric conversion element, comprising a region which contains concentrations of impurities that satisfy the following relations:

$[O_i] \geq 2E17 \text{ [atoms/cm}^3\text{]}$ (Condition 1a) and

$[C] \leq 1E17 \text{ [atoms/cm}^3\text{]}$ (Condition 2)

where $[O_i]$ is an interstitial oxygen concentration determined by Fourier transform infrared spectroscopy and [C] is a total carbon concentration determined by secondary ion mass spectrometry;

wherein the polycrystalline silicon ingot is doped with boron.

8. (Previously presented) A polycrystalline silicon ingot for use in a photoelectric conversion element, comprising a region which contains concentrations of impurities that satisfy the following relations:

$[O_i] + 3 \times [N] \geq 2E17 \text{ [atoms/cm}^3\text{]}$ (Condition 1b) and

$[C] \leq 1E17 \text{ [atoms/cm}^3\text{]}$ (Condition 2)

where $[O_i]$ is an interstitial oxygen concentration determined by Fourier transform infrared spectroscopy, [N] is a total nitrogen concentration determined by secondary ion mass spectrometry, and [C] is a total carbon concentration determined by secondary ion mass spectrometry;

wherein the polycrystalline silicon ingot is doped with boron.

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